

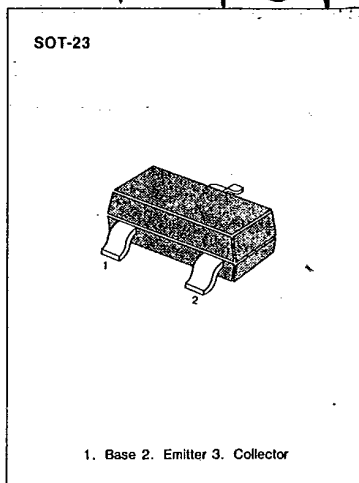
MMBA812M7**PNP EPITAXIAL SILICON TRANSISTOR****GENERAL PURPOSE TRANSISTOR****ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	50	V
Collector-Emitter Voltage	V_{CE0}	40	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	350	mW
Storage Temperature	T_{stg}	150	$^\circ\text{C}$

• Refer to MMBT5086 for graphs

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CB0}	$V_{CB}=40\text{V}, I_E=0$		100	nA
Emitter Cutoff Current	I_{EB0}	$V_{EB}=5\text{V}, I_C=0$		100	nA
DC Current Gain	h_{FE}	$V_{CE}=6\text{V}, I_C=1\text{mA}$	300	600	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=30\text{mA}, I_B=3\text{mA}$		0.5	V
Base-Emitter On Voltage	$V_{BE(on)}$	$I_C=1\text{mA}, V_{CE}=6\text{V}$		0.8	V

**Marking**